

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Manfred Ruehrig et al.  
Serial No.: Unknown  
(Priority Application No. DE 102 14 159.2)  
(International Application No. PCT/DE03/00775)  
Filed: Herewith  
(Priority Date: March 28, 2002)  
(International Filing Date: March 11, 2003)  
Docket No.: I433.125.101/13.305  
Title: MRAM MEMORY CELL WITH A REFERENCE LAYER AND METHOD  
FOR FABRICATING (As Amended)

---

**PRELIMINARY AMENDMENT**

Mail Stop PCT  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

This Preliminary Amendment amends the Utility Patent Application filed herewith and should be used to calculate filing fees due. Prior to examination of the above-identified patent application, please amend as follows:

**Preliminary Amendment**

Applicant: Manfred Ruehrig et al.

Serial No.: Unknown

(Priority Application No. DE 102 14 159.2)

(International Application No. PCT/DE03/00775)

Filed: Herewith

(Priority Date: March 28, 2002)

(International Filing Date: March 11, 2003)

Docket No.: I433.125.101/13.305

Title: MRAM MEMORY CELL WITH A REFERENCE LAYER AND METHOD FOR FABRICATING (As Amended)

---

**IN THE TITLE**

Please replace the title with the following rewritten title:

**METHOD FOR FABRICATING A REFERENCE LAYER AND MRAM**  
**MEMORY CELL PROVIDED WITH A REFERENCE LAYER OF THIS TYPE AND**  
**METHOD FOR FABRICATING**